Silicon Compatible Emerging Materials, Processes, and Technologies for Advanced CMOS and Post-CMOS Applications 10

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Table of Contents

Preface *iii*

Chapter 1
Heterogeneous Integration (Plenary Session)

Effect of Inductively Coupled Electro-Magnetic Field on Bottom Oxide Etch in a High Aspect Ratio Trench 3
S. Sardo, A. Palombizio, M. Mannarino, A. Redolfi, L. Haspeslagh

Chapter 2
Neuromorphic Devices, Materials, and Memory

Process Dependent Optimization of Dielectric and Metal Stacks for Multilevel Resistive Random-Access Memory 13
P. Zhao, D. Misra, D. Triyoso, V. Kaushik, K. Tapily, R. D. Clark, S. Consiglio, C. S. Wajda, G. J. Leusink

Chapter 3
Poster Session

Study on Influence of O_2 Concentration in Wafer Cleaning Ambient for Smoothness of Silicon (110) Surface Appearing at Sidewall of Three-Dimensional Transistors 23
T. Suwa, A. Teramoto, Y. Shirai, T. Matsuo, N. Mizutani, S. Sugawa

Interferometric Optical Isolator with Si Guiding Layer Operated in Unidirectional Magnetic Field 31
H. Yokoi, A. Yumoto, H. Hasegawa, S. Matsuzaki

Chapter 4
Ferroelectric and Phase Change Materials, Memory, and Technology

Switching Dynamics Measurement of Ferroelectric Y-Doped HfO_2 M-I-M Capacitor 39
Y. Lin, K. Mizutani, T. Hoshii, H. Wakabayashi, K. Tsutsui, K. Kakushima

Electrical Characterization of Sputter Deposited $Al_xSc_{1-X}N$ Thin Films 45
S. Tsai, K. Kusafuka, T. Hoshii, H. Wakabayashi, K. Tsutsui, K. Kakushima

Chapter 5
Advanced Semiconductor Materials, Devices, and Processing I

Electromigration Study of Plasma Etched Copper Lines with Copper Oxide Capping Layers 51
J. Q. Su, Y. Kuo

Chapter 6
Advanced Semiconductor Materials, Devices, and Processing 2

*(Invited)*Â Doping Considerations for Finfet, Gate-All-Around, and Nanosheet Based Devices 63
R. Duffy, F. Meaney, E. Galluccio

*(Invited)*Â Differential Hall Effect Metrology (DHEM) Sub-Nm Profiling and Its Application to Dopant Activation in n-Type Ge 75
P. Ramesh, K. C. Saraswat, A. Joshi, B. M. Basol, L. Wang, T. Buyuklimanli

BEOL Compatible High-Capacitance MIMCAP Structure Using a Novel High k Material 81
P. C. Jamison, J. Massey, T. Ando, E. A. Cartier, H. Jagannathan, P. J. Chen, E. Liu, A. Romero, S. Naczas, V. Narayanan, S. Pancharatnam, P. Restle, J. Rubin, N. J. Loubet, K. Choi

Strain Modification of PECVD Nitride By Plasma Immersion Ion Implantation Processes 93
L. Lachal, C. Plantier, F. Torregrosa, C. Aubert, J. M. Pedini, G. Borvon, M. Coig, F. Milesi, H. Niebojewski, F. Mazen